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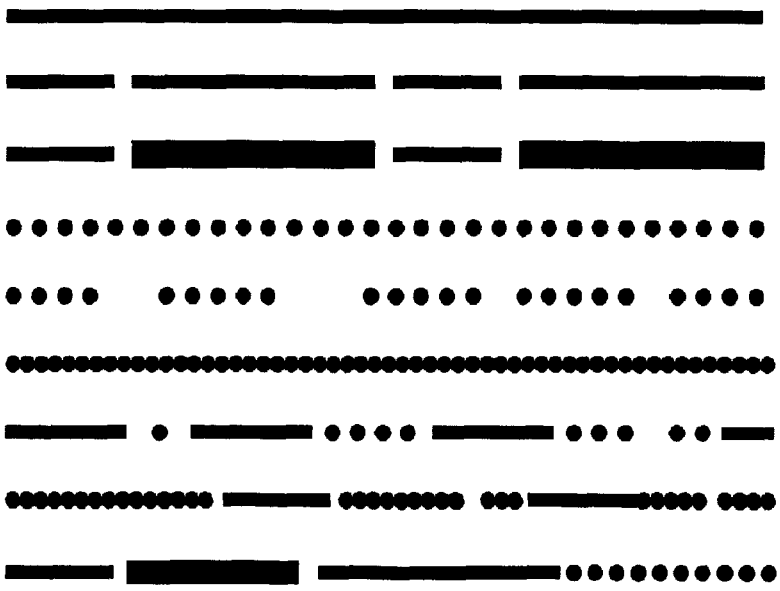
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(54) Title: CHEMICAL MECHANICAL POLISHING PAD HAVING HOLES AND/OR GROOVES



(57) Abstract: Disclosed is a chemical mechanical polishing pad formed with holes, grooves or a combination thereof. The chemical mechanical polishing pad is characterized in that a plurality of concentric circles each having grooves, holes, or a combination thereof are formed at a polishing surface of the polishing pad. The chemical mechanical polishing pad provides effects of effectively controlling a flow of slurry during a polishing process, thereby achieving a stability in the polishing process in terms of a polishing rate, and achieving an enhancement in the planarization of a wafer.

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